IXYS UK WESTCODE

Date:- 16 Aug, 2016

Data Sheet Issue:- 1

Insulated Gate Bi-Polar Transistor

Type T0500ND25E

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	2500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	1250	V
V_{GES}	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	500	A
I_{CRM}	Repetitive peak collector current, t_p=1ms, IGBT	1000	A
I_{ECO}	Maximum reverse emitter current, t_p=100µs, (note 2 & 3)	500	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	2.58	kW
T_j	Operating temperature range.	-40 to +125	°C
T_{stg}	Storage temperature range.	-40 to +125	°C

Notes: -
1) Unless otherwise indicated T_j = 125ºC.
2) T_{sink} = 25°C, double side cooled.
3) Maximum commutation loop inductance 850nH.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
$V_{CE(sat)}$	Collector – emitter saturation voltage	-	2.4	2.7	I_C = 500A, V_{GE} = 15V, T_j = 25°C	V
		-	3.05	3.35	I_C = 500A, V_{GE} = 15V	V
V_{T0}	Threshold voltage	-	-	1.39	Current range: 167A– 500A	V
r_T	Slope resistance	-	-	3.92		mΩ
$V_{GE(TH)}$	Gate threshold voltage	-	5.8	-	V_{CE} = V_{GE}, I_C = 45mA	V
I_{CES}	Collector – emitter cut-off current	-	5	15	V_{CE} = V_{CES}, V_{GE} = 0V	mA
I_{GES}	Gate leakage current	-	-	±10	V_{GE} = ±20V	µA
C_{ies}	Input capacitance	-	68	-	V_{CE} = 25V, V_{GE} = 0V, f = 100kHz, T_j=25°C	nF
$t_{d(on)}$	Turn-on delay time	-	0.9	-	I_C =500A, V_{CE} =1250V, di/dt=1000A/µs V_{GE} = ±15V, L_s=850nH $R_{g(ON)}$= 5.6Ω, $R_{g(OFF)}$= 12Ω, C_{GE}=15nF Freewheel diode type E0800QC25C at T_j=125°C	µs
t_r(V)	Rise time	-	2	-		µs
$Q_{g(on)}$	Turn-on gate charge	-	5	-		µC
E_{on}	Turn-on energy	-	0.65	-		J
$t_{d(off)}$	Turn-off delay time	-	1.1	-		µs
t_f(I)	Fall time	-	2.6	-		µs
$Q_{g(off)}$	Turn-off gate charge	-	3	-		µC
E_{off}	Turn-off energy	-	0.87	-		J
I_{SC}	Short circuit current	-	2150	-	V_{GE}=+15V, V_{CC}=1250V, V_{CEmax}≤V_{CES}, t_p≤10µs	A

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R_{thJK}	Thermal resistance junction to sink, IGBT	-	-	38.6	Double side cooled	K/kW
		-	-	60	Collector side cooled	K/kW
		-	-	108	Emitter side cooled	K/kW
F	Mounting force	8	-	12	Note 2	kN
W_t	Weight	-	0.5	-		kg

Notes:-

1) Unless otherwise indicated T_j=125°C.
2) Consult application note 2008AN01 for detailed mounting requirements
3) C_{GE} is additional gate – emitter capacitance added to output of gate drive

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

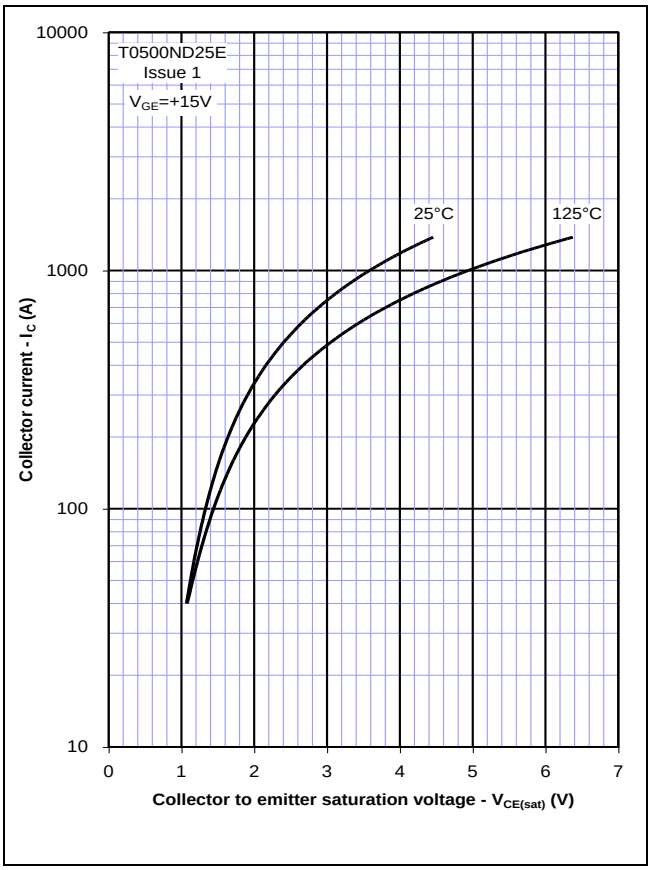


Figure 2 – Typical output characteristic

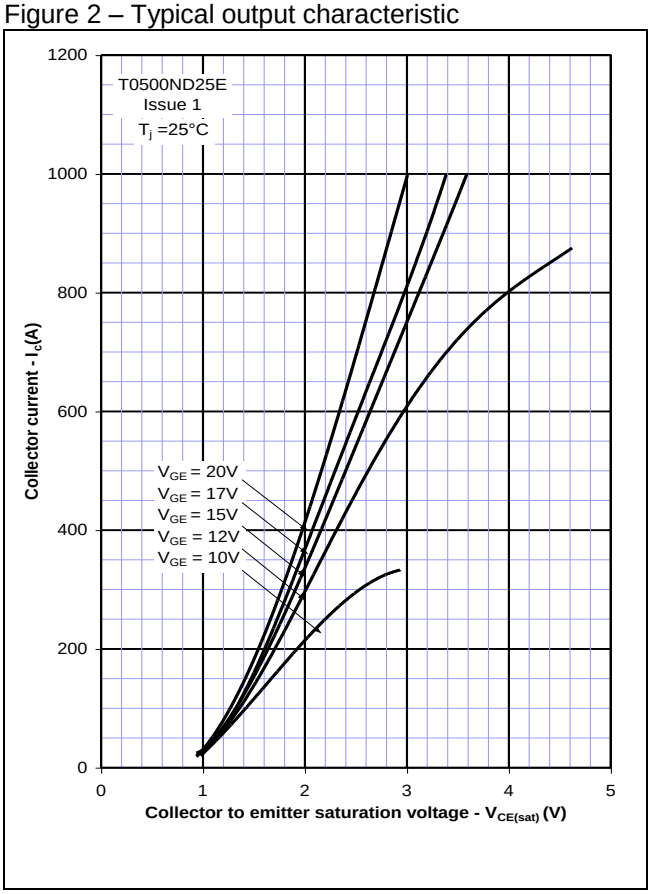


Figure 3 – Typical output characteristic

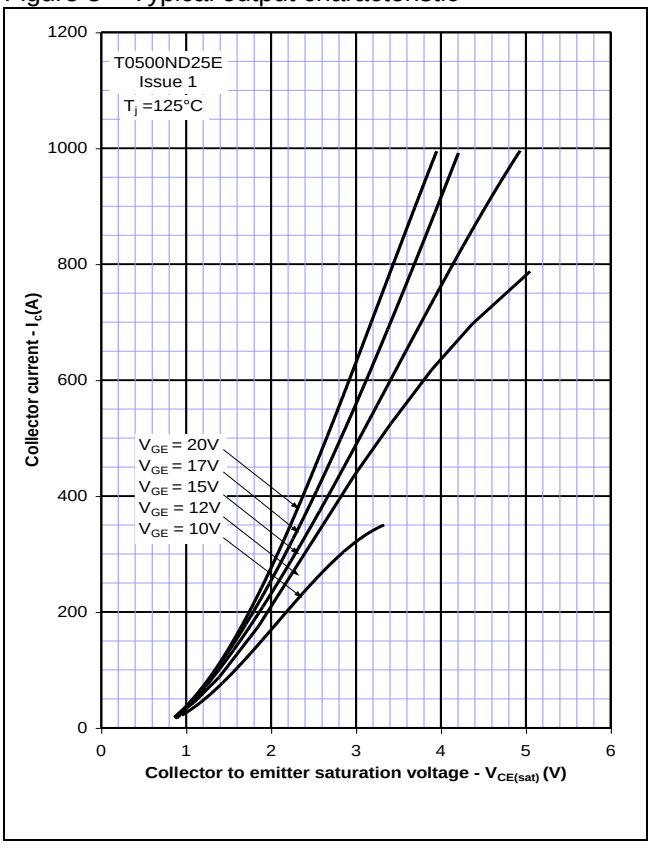


Figure 4 – Typical turn-on delay time vs gate resistance

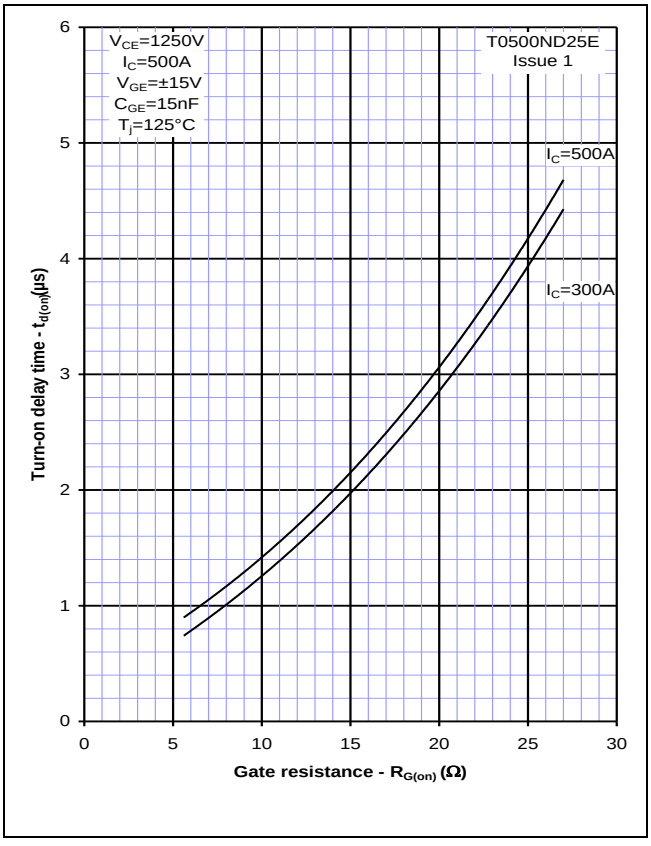


Figure 5 – Typical turn-off delay time vs. gate resistance

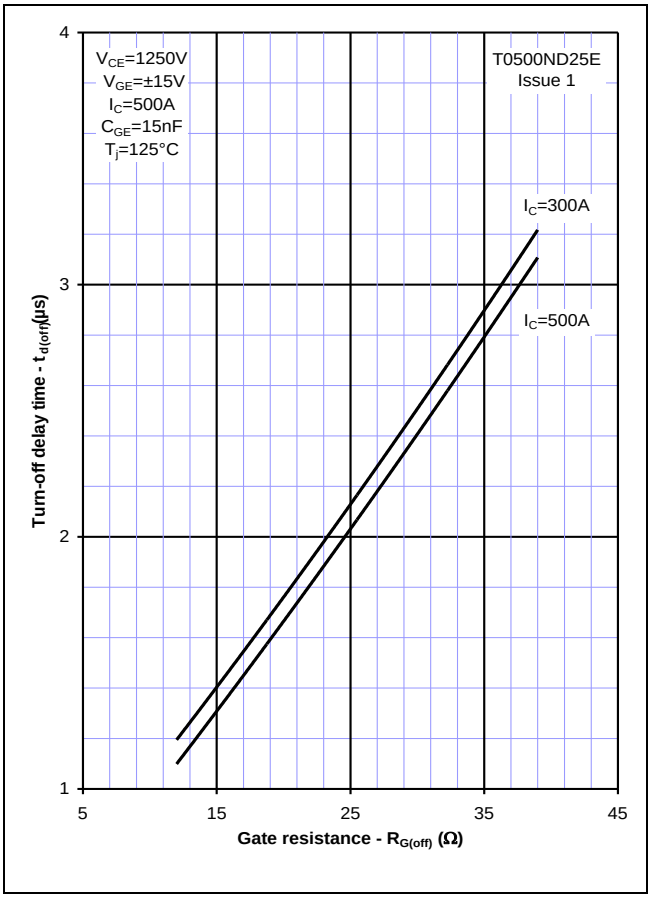


Figure 6 – Typical turn-on energy vs. collector current

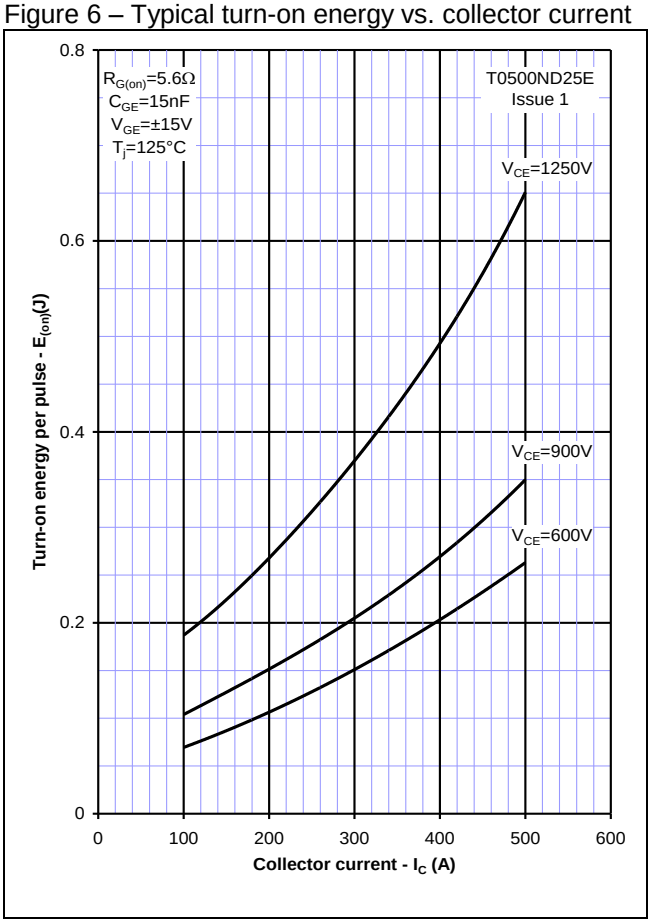


Figure 7 – Typical turn-on energy vs. di/dt

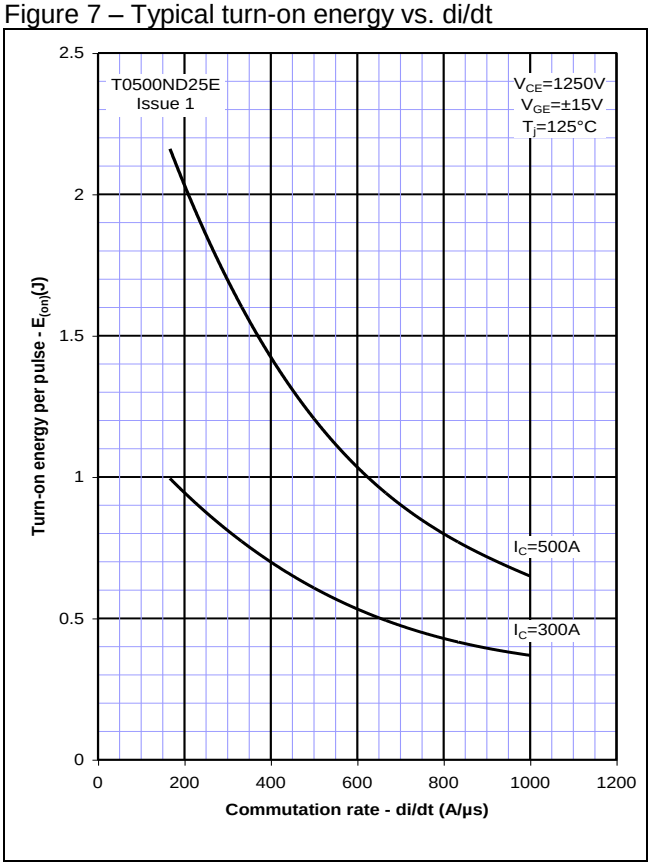


Figure 8 – Typical turn-off energy vs. collector current

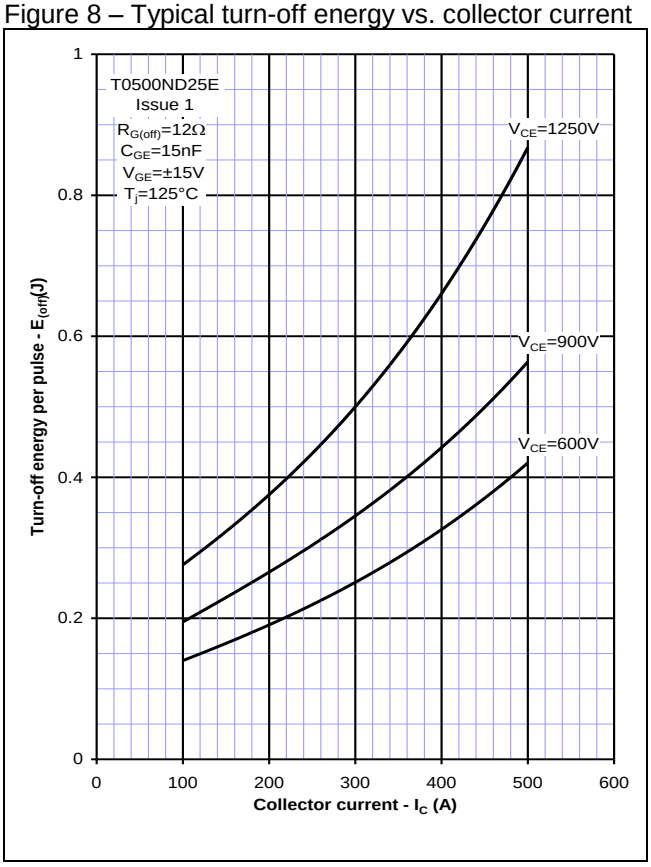


Figure 9 – Turn-off energy vs voltage

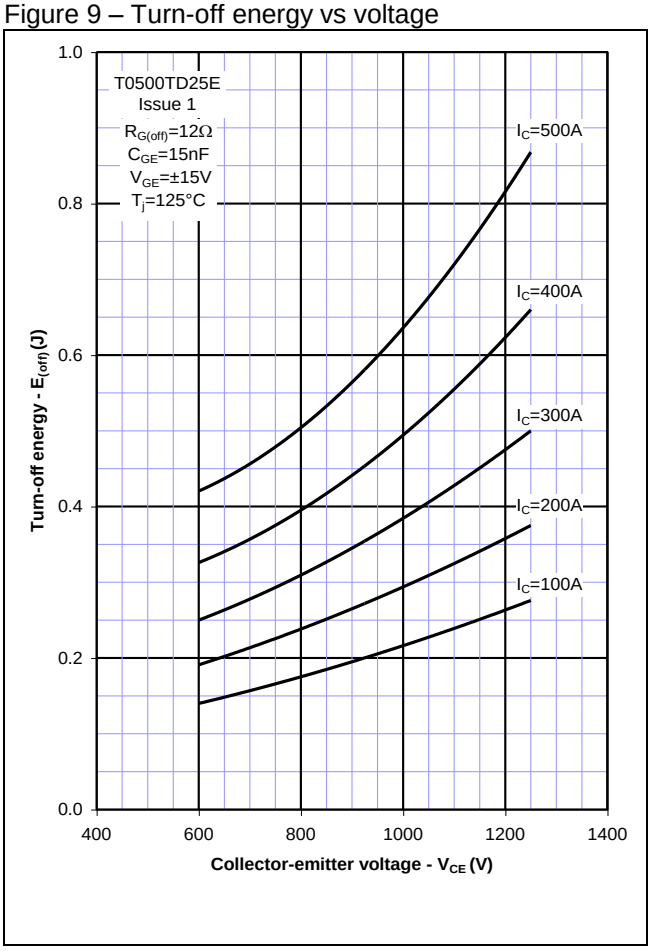


Figure 10 – Safe operating area

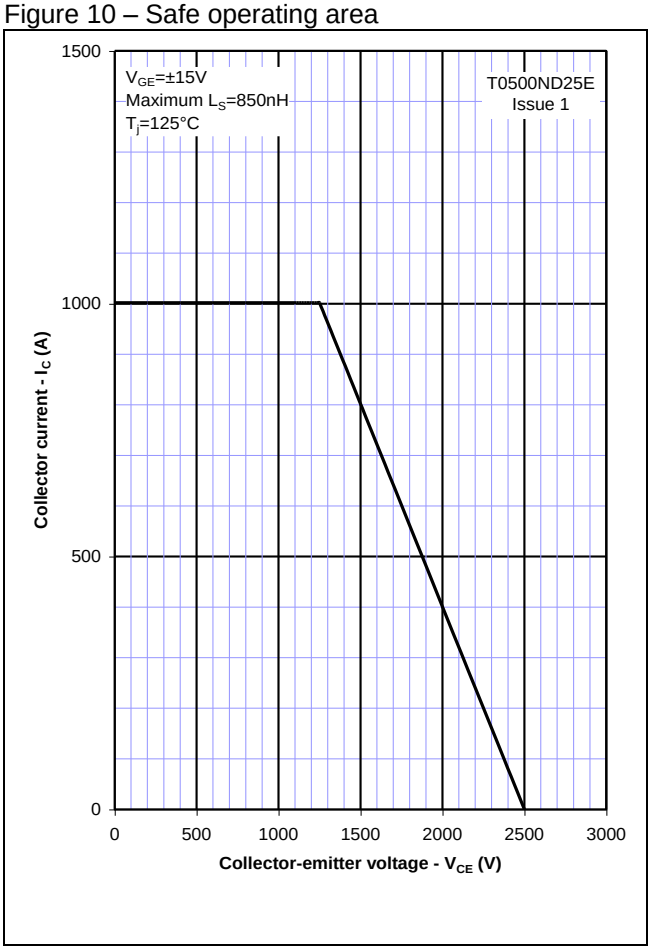
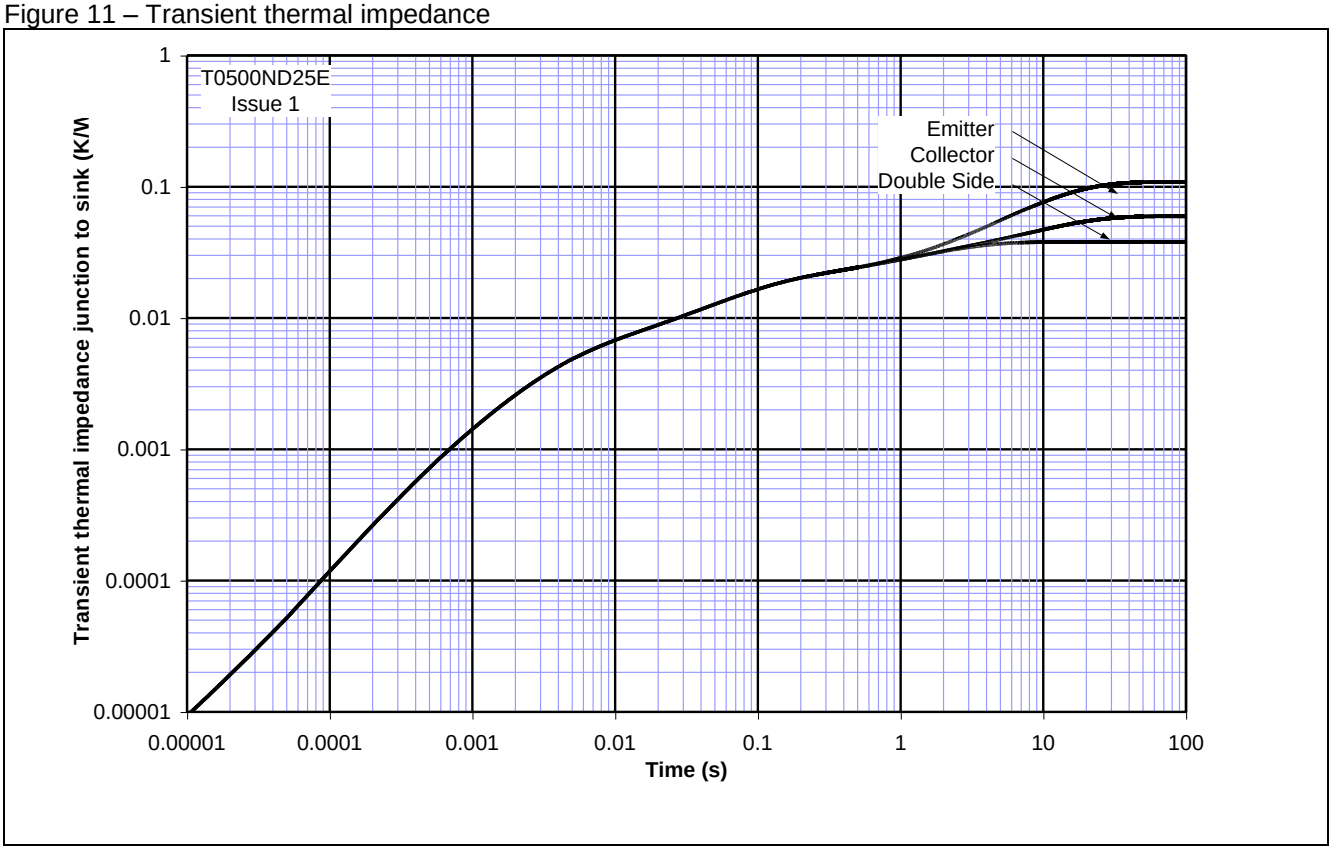
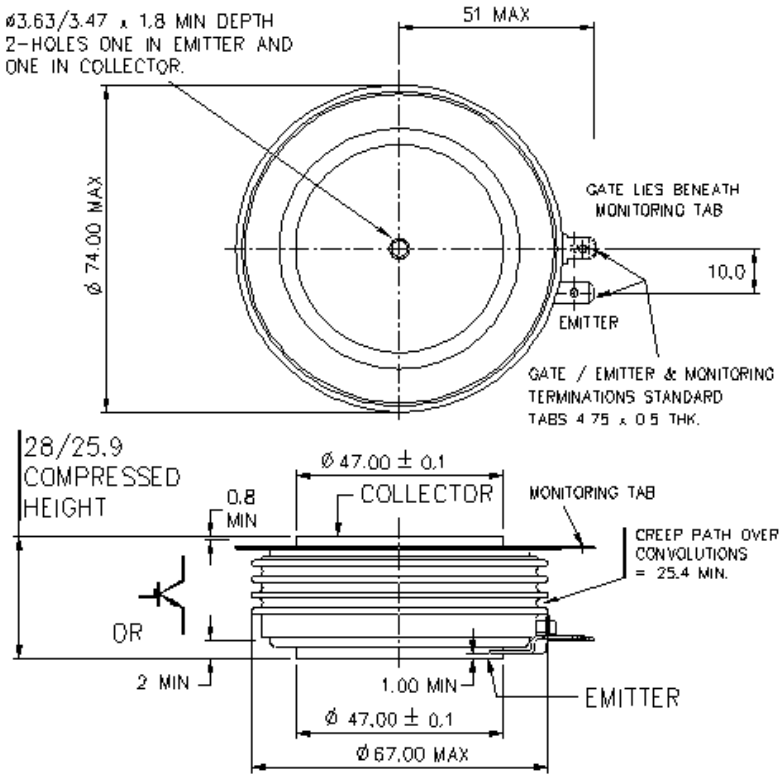


Figure 11 – Transient thermal impedance



Outline Drawing & Ordering Information



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ORDERING INFORMATION (Please quote 10 digit code as below)

T0500	ND	25	E
Fixed type Code	Fixed Outline Code	Voltage Grade V_{CES}/100 25	Fixed format code

Typical order code: T0500ND25E (V_{CES} = 2500V)

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

IXYS UK Westcode Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: sales@ixysuk.com

IXYS Corporation
1590 Buckeye Drive
Milpitas CA 95035-7418
Tel: +1 (408) 457 9000
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.ixysuk.com

www.ixys.net

IXYS Long Beach
IXYS Long Beach, Inc
2500 Mira Mar Ave, Long Beach
CA 90815
Tel: +1 (562) 296 6584
Fax: +1 (562) 296 6585
E-mail: service@ixyslongbeach.com